

IN THE CLAIMS:

Please cancel claims 25, 26, 28, 30, 33, 35 and 37 without prejudice to or disclaimer of the subject matter recited therein.

Please amend claims 27, 29, 31, 32, 34, 36 and 38 as follows:

LISTING OF CURRENT CLAIMS

Claims 1-26. (Canceled)

Claim 27. (Currently Amended) ~~The method according to claim 26, A method~~
for encapsulating a light emitting diode, which comprises the steps of:

- a) placing a crystalline grains light-emitting diode chip into a pre-punched first lead frame;
- 5 b) electrically connecting the first lead frame and the crystalline grains light-emitting diode chip to a second lead frame;
- c) encapsulating the crystalline grains light-emitting diode chip in a photosensitive polymer, the encapsulating step including placing the first lead frame, the crystalline grains light-emitting diode chip, and the
10 second lead frame in a mold and injecting the photosensitive polymer into the mold;
- d) curing the photosensitive polymer at room temperature to form an encapsulated light emitting diode; and
- e) cutting, testing and packaging the encapsulated light emitting diode,
15 wherein the photosensitive polymer utilized in the encapsulating step c)
includes an Oligomer and a Photoinitiator, wherein the photosensitive polymer
utilized in the encapsulating step c) includes at least one selected from the group
consisting of between 0.1% and 20% of a Silane coupling agent, 0.01% and 15% of
an ultraviolet absorber agent, and between 0.01% and 20% of a Hindered Amine
20 Light Stabilizer.

Claim 28. (Canceled)

Claim 29. (Currently Amended) ~~The method according to claim 28;~~ A method for encapsulating a light emitting diode, which comprises the steps of:

- a) placing a crystalline grains light-emitting diode chip into a pre-punched first lead frame;
- 5 b) electrically connecting the first lead frame and the crystalline grains light-emitting diode chip to a second lead frame;
- c) encapsulating the crystalline grains light-emitting diode chip in a photosensitive polymer, the encapsulating step including placing the first lead frame, the crystalline grains light-emitting diode chip, and the
10 second lead frame in a mold and injecting the photosensitive polymer into the mold;
- d) curing the photosensitive polymer at room temperature to form an encapsulated light emitting diode; and
- e) cutting, testing and packaging the encapsulated light emitting diode,
15 wherein the photosensitive polymer utilized in the encapsulating step c) includes a reactive Monomer and a Photoinitiator, wherein the photosensitive polymer utilized in the encapsulating step c) includes at least one selected from the group consisting of between 0.1% and 20% of a Silane coupling agent, 0.01% and 15% of an ultraviolet absorber agent, and between 0.01% and 20% of a Hindered
20 Amine Light Stabilizer.

Claim 30. (Canceled)

Claim 31. (Currently Amended) ~~The method according to claim 30;~~ A method for encapsulating a light emitting diode, which comprises the steps of:

- a) placing a crystalline grains light-emitting diode chip into a pre-punched first lead frame;
- 5 b) electrically connecting the first lead frame and the crystalline grains light-emitting diode chip to a second lead frame;
- c) encapsulating the crystalline grains light-emitting diode chip in a photosensitive polymer, the encapsulating step including placing the first lead frame, the crystalline grains light-emitting diode chip, and the

- 10 second lead frame in a mold and injecting the photosensitive polymer
 into the mold;
- d) curing the photosensitive polymer at room temperature to form an
 encapsulated light emitting diode; and
- e) cutting, testing and packaging the encapsulated light emitting diode,
15 wherein the photosensitive polymer utilized in the encapsulating step c)
 includes an Oligomer, a reactive Monomer, and a Photoinitiator, wherein the
 photosensitive polymer utilized in the encapsulating step c) includes at least one
 selected from the group consisting of between 0.1% and 20% of a Silane coupling
 agent, 0.01% and 15% of an ultraviolet absorber agent, and between 0.01% and
20 20% of a Hindered Amine Light Stabilizer.

Claim 32. (Currently Amended) ~~The method according to claim 25;~~ A method
for encapsulating a light emitting diode, which comprises the steps of:

- a) placing a crystalline grains light-emitting diode chip into a pre-punched
 first lead frame;
- 5 b) electrically connecting the first lead frame and the crystalline grains
 light-emitting diode chip to a second lead frame;
- c) encapsulating the crystalline grains light-emitting diode chip in a
 photosensitive polymer, the encapsulating step including placing the
 first lead frame, the crystalline grains light-emitting diode chip, and the
10 second lead frame in a mold and injecting the photosensitive polymer
 into the mold;
- d) curing the photosensitive polymer at room temperature to form an
 encapsulated light emitting diode; and
- e) cutting, testing and packaging the encapsulated light emitting diode,
15 wherein the photosensitive polymer utilized in the encapsulating step c)
 includes at least one selected from the group consisting of between 0.1% and 20%
 of a Silane coupling agent, 0.01% and 15% of an ultraviolet absorber agent, and
 between 0.01% and 20% of a Hindered Amine Light Stabilizer.

Claim 33. (Canceled)

Claim 34. (Currently Amended) ~~The method according to claim 33;~~ A method for encapsulating a light emitting diode, which comprises the steps of:

- a) placing a crystalline grains light-emitting diode chip into a pre-punched first lead frame;
- 5 b) electrically connecting the first lead frame and the crystalline grains light-emitting diode chip to a second lead frame;
- c) encapsulating the crystalline grains light-emitting diode chip in a photosensitive polymer, the encapsulating step including placing the first lead frame, the crystalline grains light-emitting diode chip, and the
10 second lead frame in a mold and injecting the photosensitive polymer into the mold;
- d) curing the photosensitive polymer at room temperature to form an encapsulated light emitting diode; and
- e) cutting, testing and packaging the encapsulated light emitting diode,
15 wherein the curing step d) includes exposing the photosensitive polymer to a visible light, wherein the curing step d) the photosensitive polymer is exposed to the visible light for a period of time between 5 seconds and 10 seconds.

Claim 35. (Canceled)

Claim 36. (Currently Amended) ~~The method according to claim 35;~~ A method for encapsulating a light emitting diode, which comprises the steps of:

- a) placing a crystalline grains light-emitting diode chip into a pre-punched first lead frame;
- 5 b) electrically connecting the first lead frame and the crystalline grains light-emitting diode chip to a second lead frame;
- c) encapsulating the crystalline grains light-emitting diode chip in a photosensitive polymer, the encapsulating step including placing the first lead frame, the crystalline grains light-emitting diode chip, and the
10 second lead frame in a mold and injecting the photosensitive polymer into the mold;

- d) curing the photosensitive polymer at room temperature to form an encapsulated light emitting diode; and
- e) cutting, testing and packaging the encapsulated light emitting diode,
- 15 wherein the curing step d) includes exposing the photosensitive polymer to an ultraviolet light, wherein the curing step d) the photosensitive polymer is exposed to the ultraviolet light for a period of time between 5 seconds and 10 seconds.

Claim 37. (Canceled)

Claim 38. (Currently Amended) ~~The method according to claim 37,~~ A method for encapsulating a light emitting diode, which comprises the steps of:

- a) placing a crystalline grains light-emitting diode chip into a pre-punched first lead frame;
- 5 b) electrically connecting the first lead frame and the crystalline grains light-emitting diode chip to a second lead frame;
- c) encapsulating the crystalline grains light-emitting diode chip in a photosensitive polymer, the encapsulating step including placing the first lead frame, the crystalline grains light-emitting diode chip, and the
- 10 second lead frame in a mold and injecting the photosensitive polymer into the mold;
- d) curing the photosensitive polymer at room temperature to form an encapsulated light emitting diode; and
- e) cutting, testing and packaging the encapsulated light emitting diode,
- 15 wherein the curing step d) includes exposing the photosensitive polymer to an electron beam, wherein the curing step d) the photosensitive polymer is exposed to the electron beam for a period of time between 5 seconds and 10 seconds.